

14th RD50 Workshop

Thursday 4 June 2009

Defect and Material Characterization (14:45 - 18:00)

time	[id] title	presenter
14:45	[25] Prediction of the macroscopic "reverse annealing" using microscopic defect concentrations	JUNKES, Alexandra
15:05	[4] Annealing induced evolution of defect centers in epitaxial silicon irradiated with high proton fluences	KAMINSKI, Pawel
15:25	Coffee break	
15:55	[20] TSC studies on MCz silicon pad detectors irradiated with neutrons	SCARINGELLA, Monica
16:15	[13] Comparative study of the electric field dependent variations of carrier recombination and drift parameters in MCZ Si detectors irradiated by different fluences of neutrons	Prof. VAITKUS, Juozas
16:35	[17] Effect of microscopic defects in n-type irradiated MCz silicon detectors: Impact on macroscopic parameters	Dr SRIVASTAVA, Ajay Kumar
16:55	[19] Carrier lifetime variations in MCZ Si during irradiation by 3 - 8 MeV protons at temperatures in the range of 40 -300 K	Prof. VAITKUS, Juozas
17:15	[32] Discussion Session	